

Kingtronics® Kt®

BC807

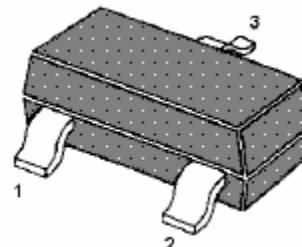
PNP Silicon Epitaxial Planar Transistors

For switching, AF driver and amplifier applications

These transistors are subdivided into three groups

-16, -25 and -40, according to their current gain.

As complementary types the NPN transistors BC817 and BC818 are recommended.



1.Base 2.Emitter 3.Collector
SOT-23 Plastic Package

Absolute Maximum Ratings (Ta = 25°C)

PARAMETER	SYMBOL	VALUE	UNIT
Collector Base Voltage	-V _{CBO}	50	V
Collector Emitter Voltage	-V _{CEO}	45	V
Emitter Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	500	mA
Power Dissipation	P _{tot}	200	mW
Thermal Resistance Junction to Ambient Air	R _{θJA}	500	K/W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _S	- 55 to + 150	°C

Electrical Characteristics at Ta = 25°C

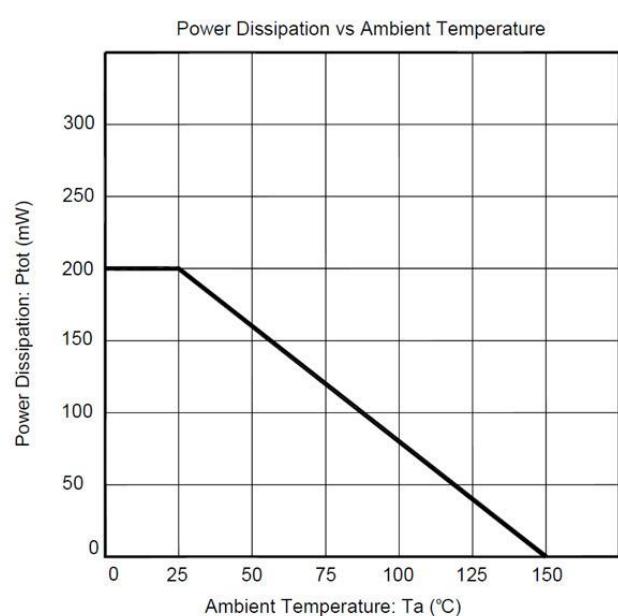
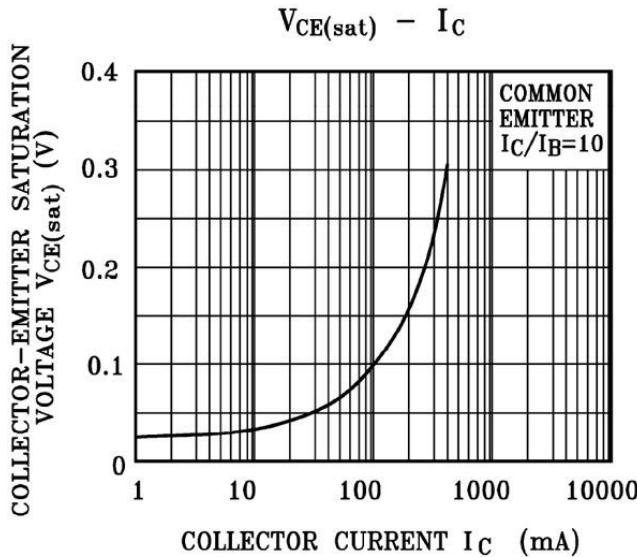
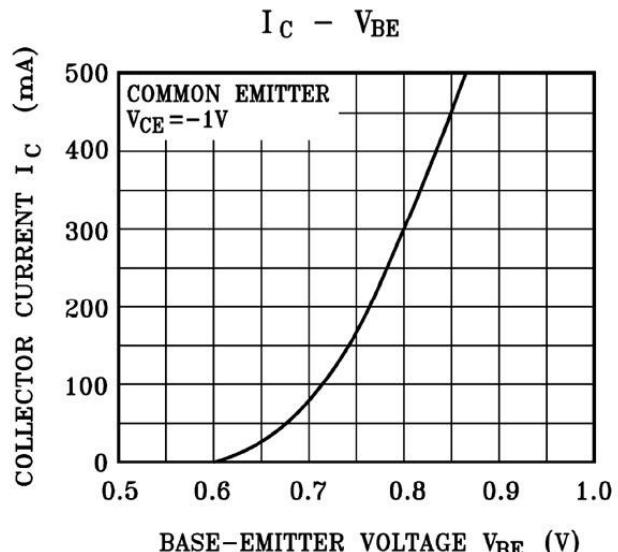
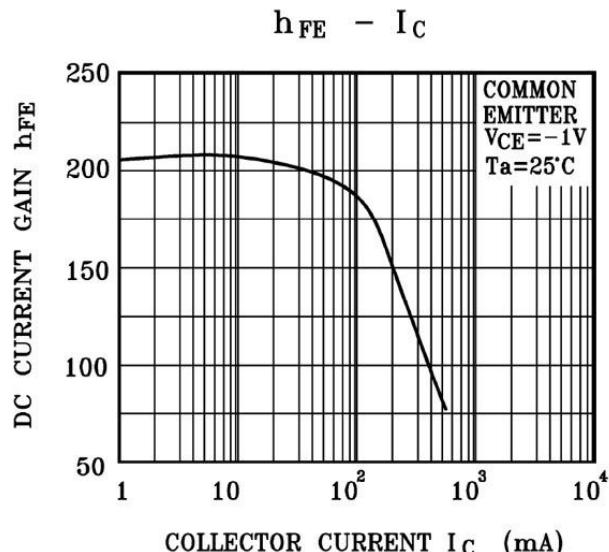
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
DC Current Gain at -V _{CE} = 1 V, -I _C = 100 mA	h _{FE}	100	16	250	
		160	-25	400	
		250	-40	600	
at -V _{CE} = 1 V, -I _C = 500 mA		40		-	
Collector Base Cutoff Current at -V _{CB} = 20 V	-I _{CBO}	-	-	100	nA
Emitter-Base Cutoff Current at -V _{EB} = 5 V	-I _{EBO}	-	-	100	nA
Collector Saturation Voltage at -I _C = 500 mA, -I _B = 50 mA	-V _{CEsat}	-	-	0.7	V
Base-Emitter Voltage at -I _C = 500 mA, -V _{CE} = 1 V	-V _{BE(on)}	-	-	1.2	V
Gain-Bandwidth Product at -V _{CE} = 5 V, -I _C = 10 mA, f = 50 MHz	f _t	80	-	-	MHz
Collector-Base Capacitance at -V _{CB} = 10 V, f = 1 MHz	C _{CBO}	-	9	-	pF

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RATINGS AND CHARACTERISTIC CURVES BC807



Note: Specifications are subject to change without notice.